

L Number	Hits	Search Text	DB	Time stamp
1	1210	(ion adj implanter) and substrate	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/05/13 14:48
2	1080	((ion adj implanter) and substrate) and semiconductor	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/05/13 14:48
3	0	((((ion adj implanter) and substrate) and semiconductor) and (shadow adj jig)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/05/13 14:49
4	50	((((ion adj implanter) and substrate) and semiconductor) and shadow	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/05/13 15:16
5	13	(((((ion adj implanter) and substrate) and semiconductor) and shadow ) and rotat\$3	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/05/13 15:10
6	50	((ion adj implanter) and substrate) and shadow	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/05/13 15:06
7	7	(((((ion adj implanter) and substrate) and semiconductor) and shadow ) and tilt\$3	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/05/13 15:10
8	34	(((((ion adj implanter) and substrate) and semiconductor) and shadow ) and (dosage or dose)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/05/13 15:12
9	14	(((((ion adj implanter) and substrate) and semiconductor) and shadow ) and (ion near4 (dosage or dose))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/05/13 15:12
10	16	((ion adj implanter) and substrate) and (shadow near4 substrate)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/05/13 15:18

L Number	Hits	Search Text	DB	Time stamp
1	23	"5343047" "5841969"	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/05/13 17:46
-	1210	(ion adj implanter) and substrate	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/05/13 14:48
-	1080	((ion adj implanter) and substrate) and semiconductor	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/05/13 14:48
-	0	((((ion adj implanter) and substrate) and semiconductor) and (shadow adj jig)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/05/13 14:49
-	50	((((ion adj implanter) and substrate) and semiconductor) and shadow	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/05/13 15:16
-	13	(((((ion adj implanter) and substrate) and semiconductor) and shadow ) and rotat\$3	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/05/13 15:10
-	50	((ion adj implanter) and substrate) and shadow	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/05/13 15:06
-	7	(((((ion adj implanter) and substrate) and semiconductor) and shadow ) and tilt\$3	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/05/13 15:10
-	34	(((((ion adj implanter) and substrate) and semiconductor) and shadow ) and (dosage or dose)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/05/13 15:12
-	14	(((((ion adj implanter) and substrate) and semiconductor) and shadow ) and (ion near4 (dosage or dose))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/05/13 15:19
-	16	((ion adj implanter) and substrate) and (shadow near4 substrate)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/05/13 15:18
-	13	(((((ion adj implanter) and substrate) and semiconductor) and (beam near4 (blanking or intercepting))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/05/13 15:46